

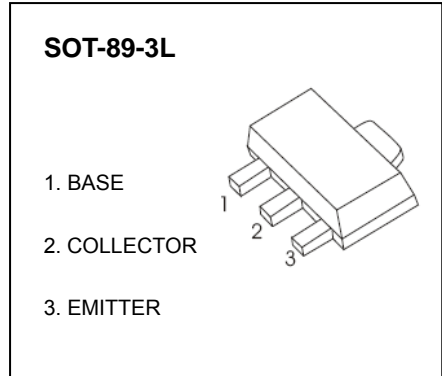
TRANSISTOR(PNP)

FEATURES

- Switching and Linear Amplification
- High Current and Low Voltage
- Complement to PXT2222A

MARKING:p2F

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)



Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-60	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-600	mA
P _C	Collector Power Dissipation	500	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	250	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-1mA, I _E =0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-1mA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0			-0.01	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.01	μA
DC current gain	h _{FE}	V _{CE} =-10V, I _C =-0.1mA	75			
		V _{CE} =-10V, I _C =-1mA	100			
		V _{CE} =-10V, I _C =-10mA	100			
		V _{CE} =-10V, I _C =-150mA	100		300	
		V _{CE} =-10V, I _C =-500mA	50			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA, I _B =-50mA			-1.6	V
		I _C =-150mA, I _B =-15mA			-0.4	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-500mA, I _B =-50mA			-2.6	V
		I _C =-150mA, I _B =-15mA			-1.3	V
Delay time	t _d	V _{CC} =-30V, I _C =-150mA, I _{B1} =- I _{B2} =-15mA			12	ns
Rise time	t _r				30	ns
Storage time	t _s				300	ns
Fall time	t _f				65	ns
Transition frequency	f _T		V _{CE} =-10V, I _C =-20mA, f=100MHz	200		